

### Absolute maximum ratings

( $T_a=25^\circ\text{C}$ )

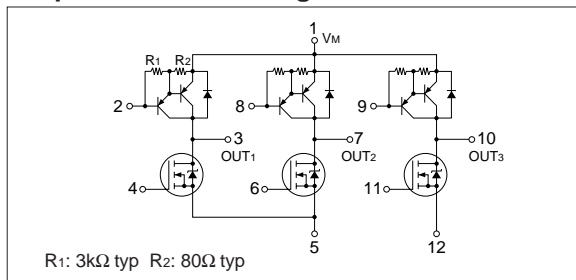
Symbol	Ratings	Unit
$V_M$	60	V
$I_o$	$\pm 6$ ( $PW \leq 100\text{ms}$ )	A
$I_{OP}$	$\pm 10$ ( $PW \leq 1\text{ms}$ )	A
$V_{GS}$	$\pm 10$	V
$I_B$	-0.5	A
$P_T$	5 ( $T_a=25^\circ\text{C}$ )	W
	35 ( $T_c=25^\circ\text{C}$ )	
$\theta_{j-a}$	25	$^\circ\text{C}/\text{W}$
$\theta_{j-c}$	3.57	$^\circ\text{C}/\text{W}$
$V_{ISO}$	1000 (Between fin and lead pin, AC)	$V_{rms}$
$T_j$	150	$^\circ\text{C}$
$T_{stg}$	-40 to +150	$^\circ\text{C}$

### Electrical characteristics (Sink : N channel MOSFET)

( $T_a=25^\circ\text{C}$ )

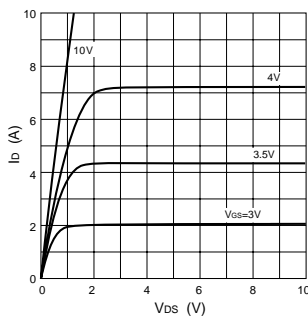
Symbol	Specification			Unit	Conditions
	min	typ	max		
$V_{(BR)DSS}$	60			V	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$
$I_{GSS}$			$\pm 500$	nA	$V_{GS}=\pm 10\text{V}$
$I_{DSS}$			250	$\mu\text{A}$	$V_{DS}=60\text{V}$ , $V_{GS}=0\text{V}$
$V_{TH}$	1.0		2.0	V	$V_{DS}=10\text{V}$ , $I_D=250\mu\text{A}$
$Re(yfs)$	3.1	4.6		S	$V_{DS}=10\text{V}$ , $I_D=4\text{A}$
$R_{DS(ON)}$		0.17	0.22	W	$V_{GS}=10\text{V}$ , $I_D=4\text{A}$
		0.25	0.30		$V_{GS}=4\text{V}$ , $I_D=4\text{A}$
$C_{iss}$		400		pF	$V_{DS}=25\text{V}$ , $f=1.0\text{MHz}$ , $V_{GS}=0\text{V}$
$C_{oss}$		160		pF	$V_{GS}=0\text{V}$
$t_{on}$		80		ns	$I_D=4\text{A}$ , $V_{DD}=30\text{V}$ , $V_{GS}=5\text{V}$
$t_{off}$		50		ns	$V_{GS}=5\text{V}$
$V_{SD}$		1.1	1.5	V	$I_{SD}=4\text{A}$ , $V_{GS}=0\text{V}$
$t_{rr}$		150		ns	$I_F=\pm 100\text{mA}$

### Equivalent circuit diagram

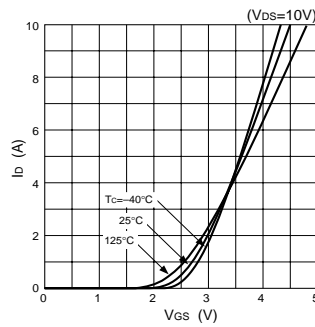


### Characteristic curves (N-channel)

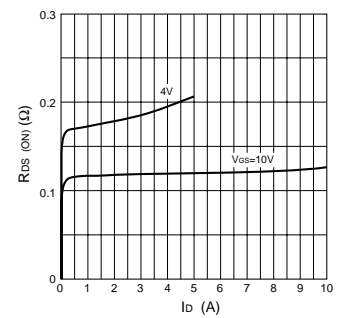
$V_{DS}-I_D$  Characteristics (Typical)



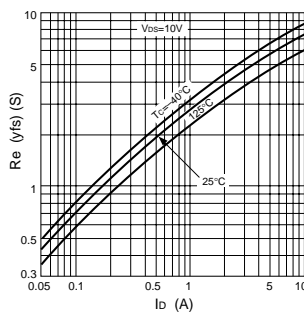
$V_{GS}-I_D$  Temperature Characteristics (Typical)



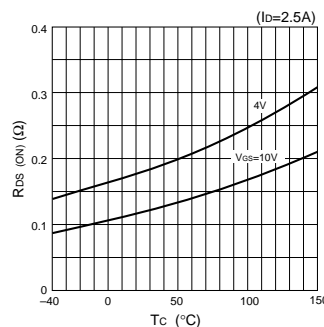
$I_{DS}-R_{DS(ON)}$  Characteristics (Typical)



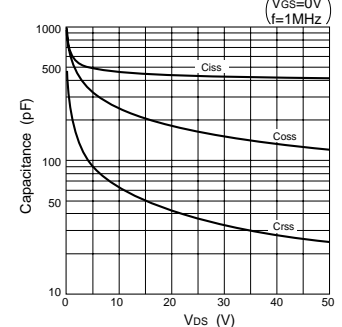
$I_D-Re(yfs)$  Temperature Characteristics (Typical)



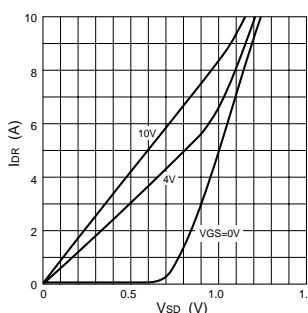
$T_c-R_{DS(ON)}$  Characteristics (Typical)



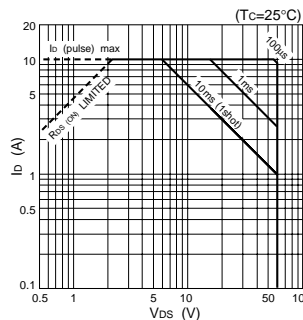
$V_{DS}-C$  Capacitance Characteristics (Typical)



$V_{SD}-I_{DR}$  Characteristics (Typical)



Safe Operating Area (SOA)

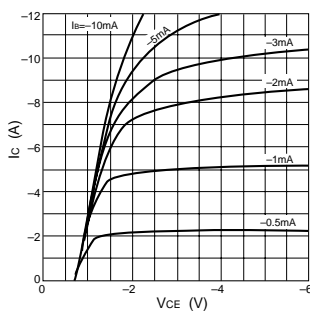


## Electrical characteristics (Source: PNP transistor) (T<sub>a</sub>=25°C)

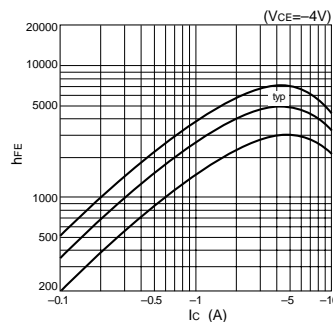
Symbol	Specification			Unit	Conditions
	min	typ	max		
I <sub>CBO</sub>			-10	μA	V <sub>CB</sub> =-60V
I <sub>EBO</sub>	-1		-5	mA	V <sub>EB</sub> =-6V
V <sub>CEO</sub>	-60			V	I <sub>C</sub> =-25mA
h <sub>FE</sub>	2000	5000	12000		V <sub>CE</sub> =-4V, I <sub>C</sub> =-4A
V <sub>CE(sat)</sub>			-1.5	V	I <sub>C</sub> =-4A, I <sub>B</sub> =-10mA
V <sub>BE(sat)</sub>			-2.0	V	
V <sub>FEC</sub>			2.0	V	I <sub>FEC</sub> =4A
t <sub>rr</sub>		1.0		μs	I <sub>F</sub> =±0.5A
t <sub>on</sub>		1.0		μs	V <sub>CC</sub> =-25V, I <sub>C</sub> =-4A,
t <sub>stg</sub>		1.4		μs	
t <sub>f</sub>		0.6		μs	I <sub>B1</sub> =-I <sub>B2</sub> =-10mA
f <sub>T</sub>		120		MHz	V <sub>CE</sub> =-12V, I <sub>E</sub> =1A
C <sub>ob</sub>		150		pF	V <sub>CB</sub> =-10V, f=1MHz

## Characteristic curves (PNP)

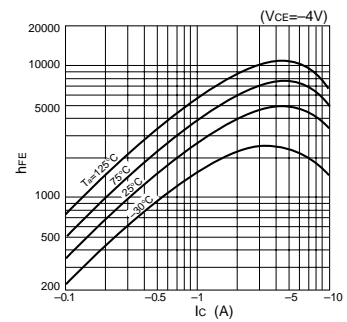
I<sub>C</sub>-V<sub>CE</sub> Characteristics (Typical)



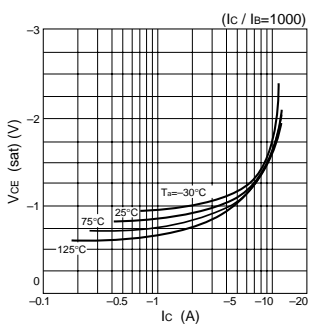
h<sub>FE</sub>-I<sub>C</sub> Characteristics (Typical)



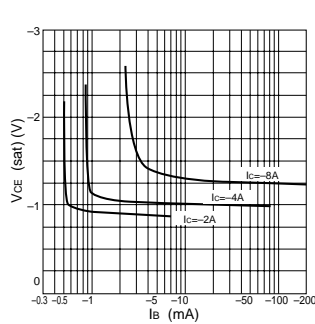
h<sub>FE</sub>-I<sub>C</sub> Temperature Characteristics (Typical)



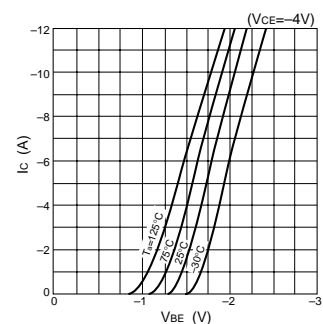
V<sub>CE(sat)</sub>-I<sub>C</sub> Temperature Characteristics (Typical)



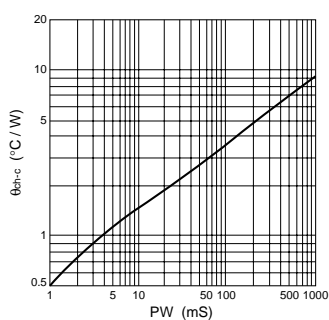
V<sub>CE(sat)</sub>-I<sub>B</sub> Characteristics (Typical)



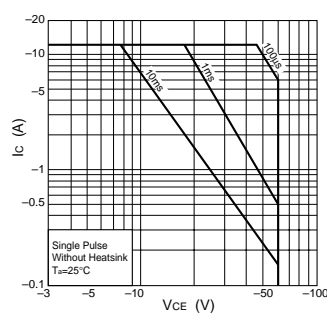
I<sub>C</sub>-V<sub>BE</sub> Temperature Characteristics (Typical)



θ<sub>j-a</sub>-PW Characteristics



Safe Operating Area (SOA)



P<sub>T</sub>-T<sub>a</sub> Characteristics

